HD31145
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB GaAsFET Chip & Wire technology
Instantaneous wide Bandwidth
Suitable for all modulation standards
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	5.0 - 18.0 GHz	
Power Output Past	10 Watt Min	CW
Small Signal Gain	40 dB Min	
Power Gain Flatness	4.0 dB p-p Max	
Input Return Loss	10 dB Min	50 Ohm reference
Harmonics	>15 dBc Typ	At rated Pout
Noise Figure	10 dB Max	
Spurious	>60 dBc	Non Harmonics
Operating Voltage	32 VDC Nom	
Current Consumption	4 Amp Max	At rated Pout
Max Input Power	+5 dBm Max	Without damage
Load VSWR Protection	5 : 1	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non Condensation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	100 X 100 X 27mm	Excluding Connectors
Weight	600 gr.	
RF Connectors In / Out	SMA female	Cover Flange
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

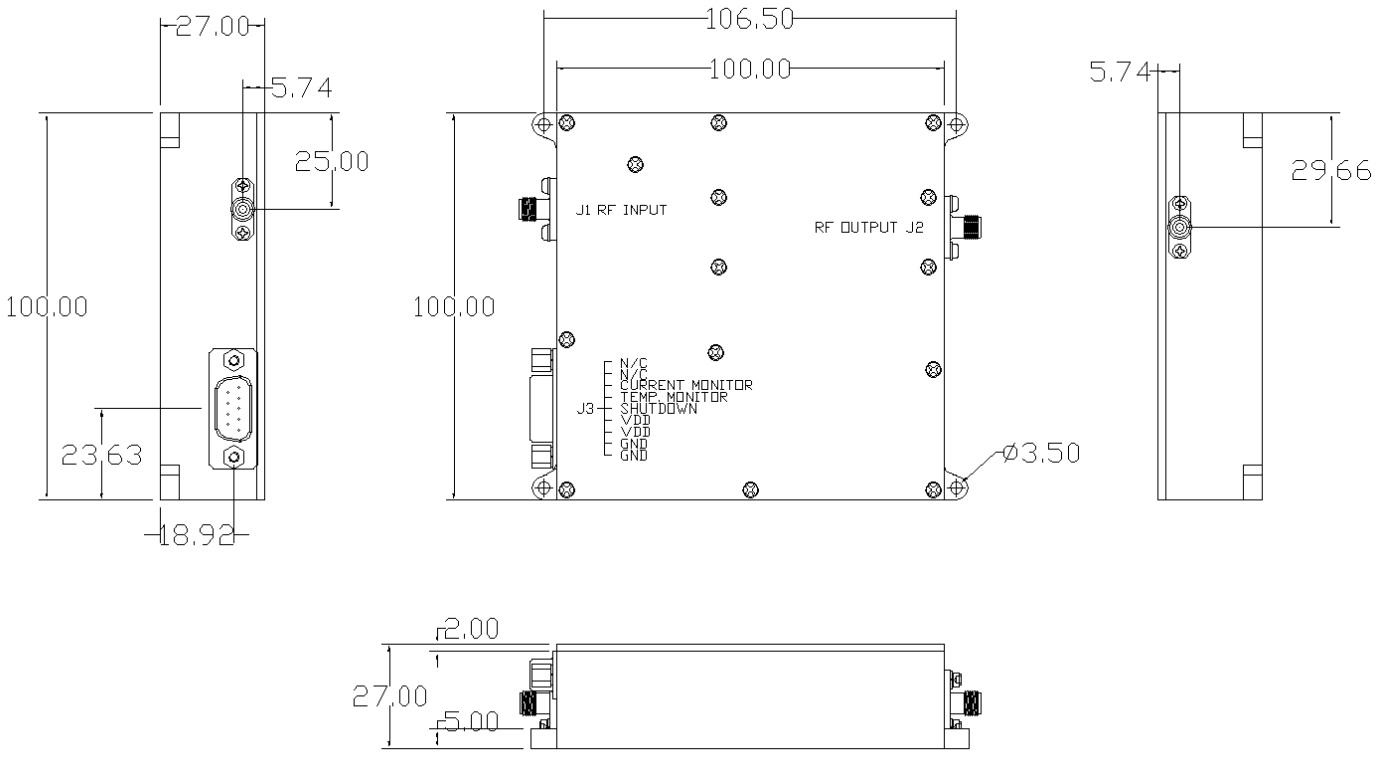
D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1		N/A
2		N/A
3	Current Sensor	I_D@20mV/100mA Typ
4	Temp Sensor	V_T@10mV/°C + 500mV Typ
5	Shutdown	TTL
6, 7	VDD	12VDC
8, 9	GND	Ground

332C Dante Ct. Holbrook, NY 11741 Phone: 631-588-3877 Fax: 631-648-0518
sales@rfamplifiers.com www.rfamplifiers.com

HD31145
SOLID STATE HIGH POWER AMPLIFIER

OUTLINE DRAWING



332C Dante Ct. Holbrook, NY 11741 Phone: 631-588-3877 Fax: 631-648-0518
sales@rfamplifiers.com www.rfamplifiers.com